Who We Are

• We are a well-established, entrepreneurial business with an industry-leading team and a profitable business.

• We’ve been a part of Cree Inc. since 1987, building the future with market-leading wide bandgap semiconductor products for the transportation, industrial, energy and communications markets.

• From young and ambitious roots in North Carolina’s Research Triangle Park, we have grown into a world-renowned commercial supplier of the fastest, most advanced wide bandgap semiconductor components and substrates available, enabling greater efficiency and performance, smaller systems and lower costs.

• **Our Mission:** lead the innovation and commercialization of SiC and GaN, liberating designers to invent power and wireless systems for a responsible, energy efficient future.

• **Our Vision:** *Powering More. Consuming Less.*

Products and Services

- **SiC MOSFETs, Modules and Diodes**
- **GaN HEMTs and MMIC Amplifiers**
- **Substrates for SiC and GaN-on-SiC power and RF power devices**
- **GaN-on-SiC Foundry:** custom GaN HEMT MMICs, including high-power amplifiers, LNA, switches and phase shifters
- **SiC power services**
Who We Serve

Communications

• MILCOM (Secure communications: handheld, man-pack, portable, vehicular, emergency services)
• SATCOM (Comms: video, Internet, voice)
• Radar (Weather, ATC, surveillance, marine)
• Telecom (4G LTE, Secure HD broadcast, CATV)

Transportation

• Automotive (EV traction motor)
• EV/HEV (On-board, offboard charging, on-board DC/DC converters)
• Traction (On-board train auxiliary power converters, air conditioning, signage, user power)

Energy

• Solar (PV string inverters, DC optimizers, micro inverters, central inverters)
• Grid (HV utility power conversion)

Industrial

• Motor (AFE regenerative drives)
• Power Supply Units
• IT Power Supplies (Servers, cloud data centers)
• UPS (High-frequency)
• Welding (Plasma welders)
• Induction Heating (High-frequency hardening/softening)
Technology Leadership

- Headquartered in Research Triangle Park, North Carolina, USA, with approximately 500 employees across nine locations on three continents
- 46,000 sq. ft. of fabrication and office facilities on 55 acres with Class 10, 100, 1000 and 10,000 clean rooms
- Accredited as a Category 1A trusted foundry by the U.S. Department of Defense

1991: Released world’s first commercial SiC wafers
1998: GaN HEMT on SiC
1999: Demonstrated 4-inch SiC wafer
2000: MMIC in GaN
2006: 1200V SiC Schottky Diode
2007: Commercial release of 100-mm, zero-micropipe SiC substrates
2008: Release of 90W GaN HEMT
2009: Record-efficiency GaN HEMT Doherty Amplifier with Digital Predistortion
2010: 1700V SiC Schottky Diode
2010: Developed high-quality 150-mm SiC substrates
2011: 1200V SiC 80mΩ MOSFET
2012: 1200V SiC half-bridge module
2014: 1700V SiC half-bridge module
2014: 1200V SiC 25mΩ MOSFET
2015: 900V SiC MOSFET
2015: Demonstrated 200-mm SiC wafer
2016: 1000V SiC MOSFET
2016: Released market’s highest-power, single-ended transistor for L-Band Radar
2017: Industry’s lowest figure-of-merit SiC MOSFET

4.9 Trillion
Total Field Hours for Wolfspeed SiC and GaN Products

15 Billion
Kilowatt Hours of Electricity that would be Saved Annually if Every Data Center Worldwide Upgraded to SiC

221 Million
Dollars of Revenue (Including Wolfspeed Materials) Earned in Fiscal 2017

2258 Patents Held and Pending by Wolfspeed

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